

Postdoctoral Research Fellow

MacDiarmid Institute for Advanced Materials and Nanotechnology

VACANCY REF: A132-09E

CLOSING DATE: 30 June 2009

Considerable progress has been made towards developing a better understanding of not only basic material properties of zinc oxide (a wide bandgap semiconductor), but also of some of the key controlling mechanisms which determine the electrical behaviour of Schottky diodes.

With the experimental demonstration of a reproducible technique for high quality ZnO Schottky diode fabrication, it is now appropriate to pursue commercially viable device designs with a view not only towards manufacturability but also performance benchmarking.

Applications are invited for a two-year fixed term postdoctoral fellowship funded through the MacDiarmid Institute for Advanced Materials and Nanotechnology (www.macdiarmid.ac.nz). The successful candidate will work alongside the team at the University of Canterbury to design, fabricate, characterise and model ZnO Schottky diode device structures for a range of applications including detection and power electronics. Experience with semiconductor device design and characterisation, excellent verbal and written communication skills, and a relevant doctoral degree are essential requirements.

For more information regarding this position please contact Assoc Prof Steven M. Durbin (steven.durbin@canterbury.ac.nz) or Dr. Martin Allen (martin.allen@canterbury.ac.nz).

Applicants must complete an on-line application form, and provide a cover letter and full curriculum vitae along with the contact details for three professional references. The on-line form can be found at <http://vacancies.canterbury.ac.nz>.

For assistance with applications, please contact the Human Resources Administrator, College of Engineering, University of Canterbury, Private Bag 4800, Christchurch, New Zealand, phone +64 3364 3473 [fax +64 3364 3881] or hr@engineering.canterbury.ac.nz.